



SDB310WAF

Schottky Barrier Diode

Features

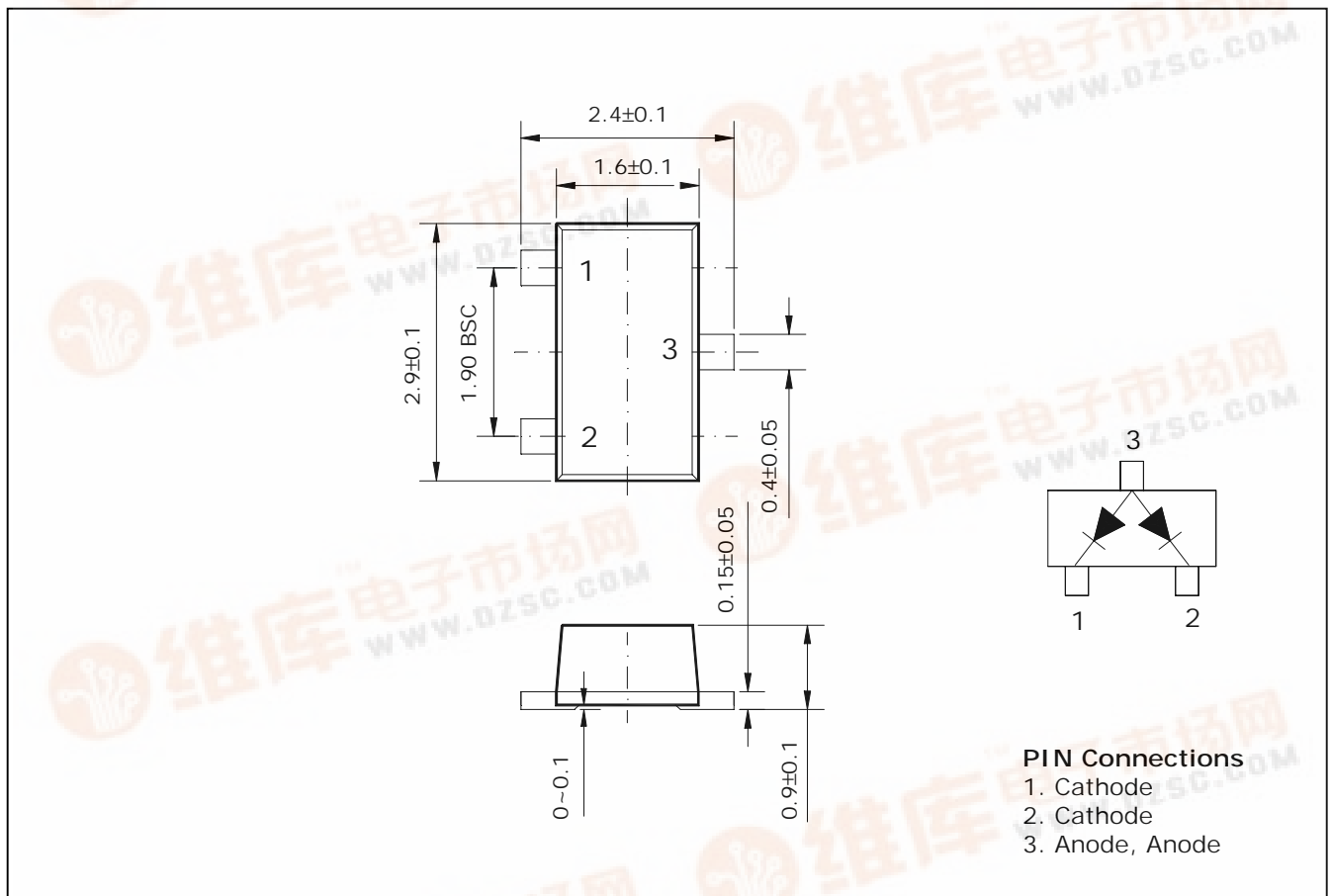
- Low power rectified
- Silicon epitaxial type
- High reliability

Ordering Information

Type No.	Marking	Package Code
SDB310WA	DB2	SOT-23F

Outline Dimensions

unit : mm



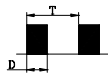
SDB310WAF

Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Reverse voltage	V _R	30	V
Repetitive peak forward current	I _{FRM} *	0.5	A
Forward current	I _F	0.2	A
Non-repetitive peak forward current(10ms)	I _{FSM}	2	A
Power dissipation	P _D	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 ~ 150	°C

* : $\delta = D/T = 0.33$
(T<1S)



* : Unit ratings. Total rating=Unit rating×1.5

Electrical Characteristics

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	V _{F(1)}	I _F =10mA	-	-	0.4	V
Forward voltage 2	V _{F(2)}	I _F =30mA	-	-	0.5	V
Reverse current	I _R	V _R =30V	-	-	1	μA
Total capacitance	C _T	V _R =1V, f=1MHz	-	-	10	pF
Reverse recovery time	t _{rr}	I _F = I _R =10mA, I _{RR} = 1mA, R _L =100Ω	-	-	5	ns

Electrical Characteristic Curves

Fig. 1 I_F - V_F

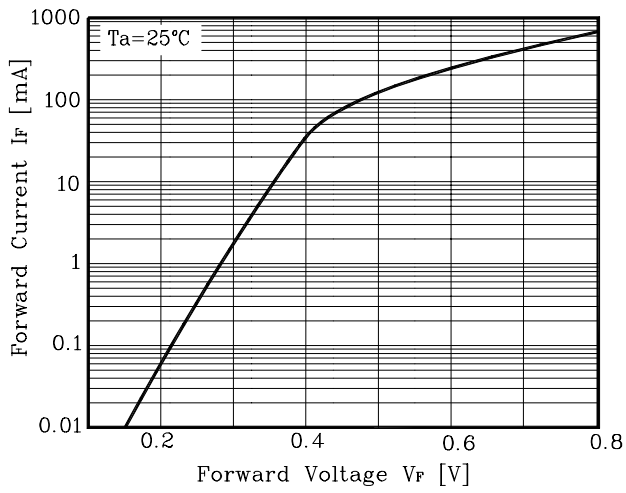


Fig. 2 I_R - V_R

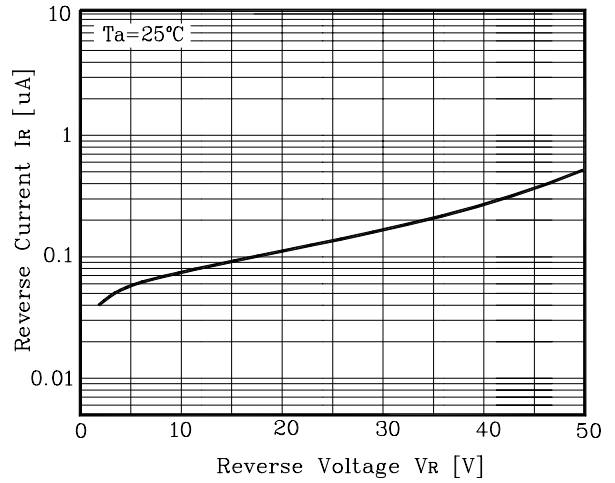


Fig. 3 C_T - V_R

